Supplementary information

Amorphous zinc-doped silicon oxide (SZO) resistive switching memory: manipulated bias control from selector to memristor

Jian-Shiou Huang, Wen-Chun Yen, Shih-Ming Lin, Chi-Yung Lee, Jiang Wu, Zhiming M. Wang, Tsung-Shune Chin, and Yu-Lun Chueh

1 Department of Materials Science and Engineering, National Tsing Hua University, Hsinchu, 30043, Taiwan
2 Department of Materials Science and Engineering, Feng Chia University, Taichung, 40724, Taiwan.
3 State Key Laboratory of Electronic Thin Films and Integrated Devices, University of Electronic Science and Technology of China, Chengdu 610054, P. R. China.

Figure S1 (a) Box chart of forming voltages at different fabrication conditions. (b) Cumulative probability of forming voltages obtained from different fabrication conditions.
Figure S2 (a) A ‘butterfly’ shape operation mode for 30 cycles. (b) 100-cycle endurance results from V-SET and i-RESET operation modes.